TECHNICAL DATA
DATA SHEET 175, REV. B

HERMETIC AXIAL LEAD/MELF RECTIFIER

DESCRIPTION: A 600 VOLT, 1.0 AMP, 250 NANOSECOND AXIAL LEAD MELF RECTIFIER

MAXIMUM RATINGS All ratings are at T_A = 25°C unless otherwise specified.

RATING	CONDITIONS	MIN.	TYP.	MAX.	UNIT
Peak Inverse Voltage (PIV)	-	-	-	600	Vdc
Average DC Output Current (I_o)	T_A = +75 °C	-	-	1.0	Amps
Average DC Output Current (I_o)	T_A = +100 °C	-	-	.75	Amps
Peak Single Cycle Surge Current (I_{fsm})	t_p = 8.3 ms Single Half Cycle Sine Wave, Superimposed On Rated Load	-	-	25	Amps(pk)
Operating and Storage Temp. (T_{op} & T_{stg})	-	-65	-	+175	°C
Thermal Resistance (θ_{JL})	d = 0.375”	-	-	38	° C/W
Thermal Resistance (θ_{JEC})	Junction to end caps	-	-	7.0	° C/W

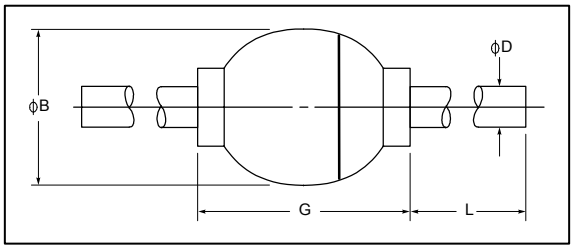
ELECTRICAL CHARACTERISTICS

CHARACTERISTIC	CONDITIONS	MIN.	TYP.	MAX.	UNIT
Maximum Forward Voltage (V_f)	I_f = 3.0A (300 µsec pulse, duty cycle < 2%)	-	-	1.6	Volts
Maximum Instantaneous Reverse Current At Rated PIV (I_R)	T_A = 25° C T_A = 100° C	-	-	0.5 25	µAmps
Reverse Recovery Time (t_{rr})	I_f = 0.5A, I_r = 0.5A, I_{rr} = 50mA	-	-	250	nsec

SENSITRON

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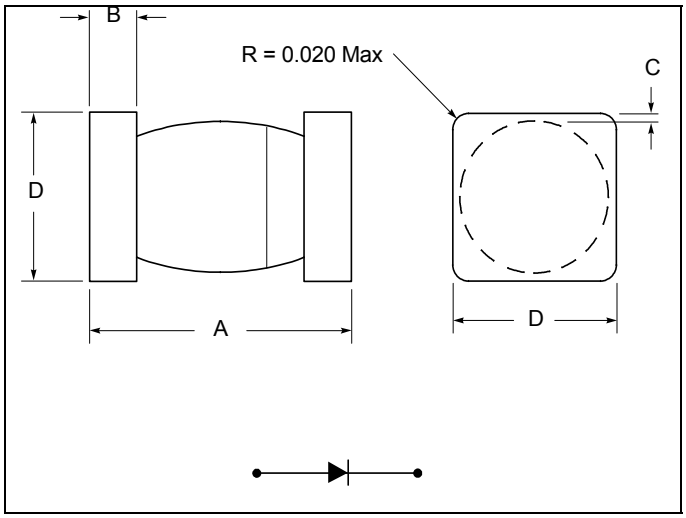
AXIAL LEAD RECTIFIER OUTLINES



Note: Cathode side of device is indicated by a dark band marked on body.

PACKAGE STYLE	DIMENSIONS - INCHES / MILLIMETERS			
	ϕB	ϕD	G	L
102	.065/.110 1.65/2.79	.026/.033 .66/.84	.130/.225 3.30/5.72	1.00/1.30 25.4/33.0

MELF PACKAGE OUTLINES



Note: Cathode side of device is indicated by a dark band marked on body.

PACKAGE STYLE	DIMENSIONS - INCHES / MILLIMETERS			
	A	B	C	D
MELF-1	.168/.230 4.2/5.9	0.019/.028 .48/.72	.003 Min .076 Min	.091/.128 3.4/3.8

SENSITRON

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